1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in an ultra small SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic-level compatible
- · Very fast switching
- · Trench MOSFET technology
- · ESD protection up to 2 kV

3. Applications

- Relay driver
- · High-speed line driver
- Low-side loadswich
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor	Per transistor								
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	-	60	V		
V_{GS}	gate-source voltage			-20	-	20	V		
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	340	mA		
Static characte	Static characteristics (per transistor)								
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.01; T_{j} = 25 °C		-	1	1.6	Ω		

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



60 V, 340 mA dual N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		
2	G1	gate1		1 + 6
3	D2	drain2	6 5 4	
4	S2	source2		2 5
5	G2	gate2		- ·
6	D1	drain1	1 2 3 SOT666	017aaa055

6. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
2N7002BKV	SOT666	plastic, surface-mounted package; 6 leads; 0.5 mm pitch; 1.6 mm x 1.2 mm x 0.55 mm body	SOT666			

7. Marking

Table 4. Marking codes

Type number	Marking code
2N7002BKV	ZG

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	tor			<u> </u>		
V _{DS}	drain-source voltage	T _{amb} = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	340	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	240	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	1.2	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	350	mW
			[1]	-	410	mW
		T _{sp} = 25 °C		-	1140	mW
Per device						<u>'</u>
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	525	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode			1		'
Is	source current	T _{amb} = 25 °C	[1]	-	340	mA
ESD maxim	num rating		'	'	'	1
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2	kV

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

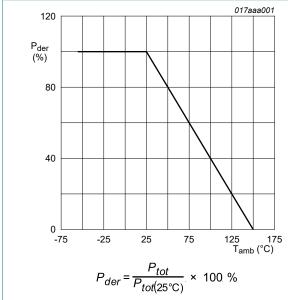


Fig. 1. Normalized total power dissipation as a function of ambient temperature

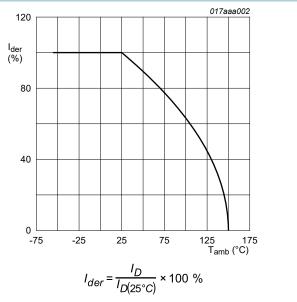
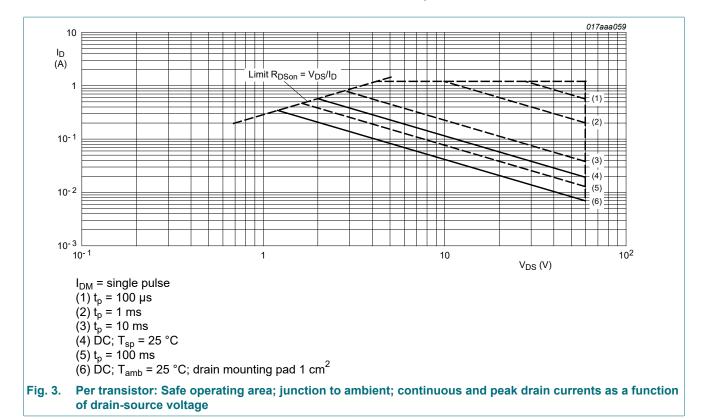


Fig. 2. Normalized continuous drain current as a function of ambient temperature

60 V, 340 mA dual N-channel Trench MOSFET



60 V, 340 mA dual N-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device					·		
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	240	K/W
Per transistor			'				
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	315	360	K/W
()			[2]	-	265	305	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	110	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

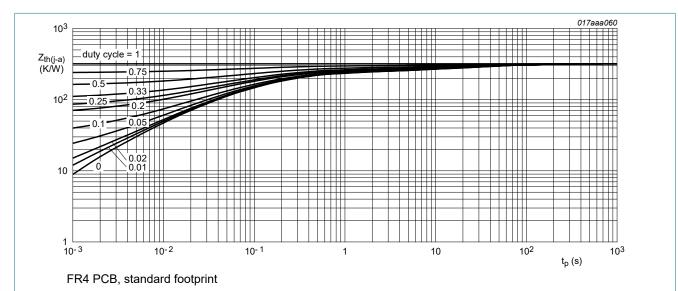


Fig. 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

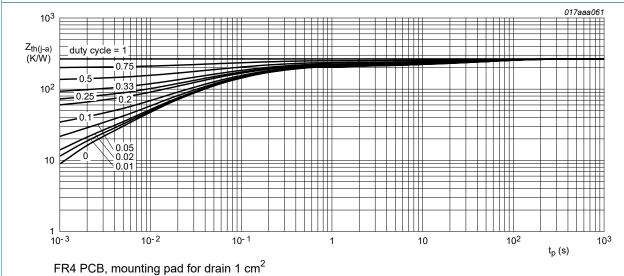


Fig. 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

2N7002BK\

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 10 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
R _{DSon} drain-source on-s resistance	drain-source on-state resistance	V_{GS} = 5 V; I_{D} = 50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.01; T_{j} = 25 °C	-	1.3	2	Ω
		V_{GS} = 10 V; I_D = 500 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.01; T_j = 25 °C	-	1	1.6	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 200 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.01; T_{j} = 25 °C	-	550	-	mS
Dynamic ch	aracteristics (per transist	or)				
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 300 mA; V _{GS} = 4.5 V;	-	0.5	0.6	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.2	-	nC
Q _{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	33	50	рF
C _{oss}	output capacitance	T _j = 25 °C	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 250 \Omega; V_{GS} = 10 \text{ V};$	-	5	10	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	6	-	ns
t _{d(off)}	turn-off delay time		-	12	24	ns
t _f	fall time		-	7	-	ns
Source-drai	in diode (per transistor)					
V_{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _i = 25 °C	0.47	0.75	1.1	V

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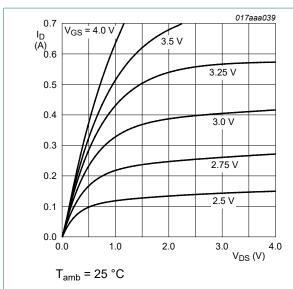
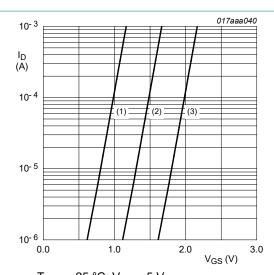


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

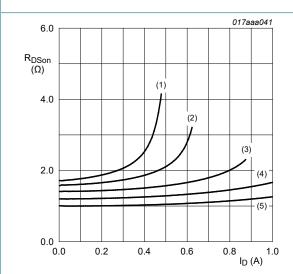


 T_{amb} = 25 °C; V_{DS} = 5 V (1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



 T_{amb} = 25 °C

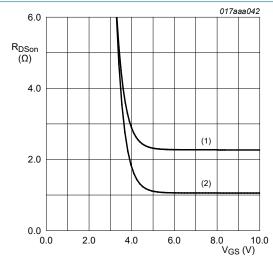
(1) $V_{GS} = 3.25 \text{ V}$

 $(2) V_{GS} = 3.5 V$

(3) $V_{GS} = 4 V$ (4) $V_{GS} = 5 V$

 $(5) V_{GS} = 10 V$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 500 \text{ mA}$

(1) T_{amb} = 150 °C

 $(2) T_{amb} = 25 °C$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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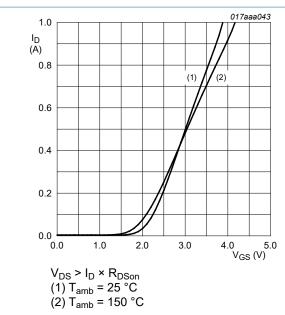
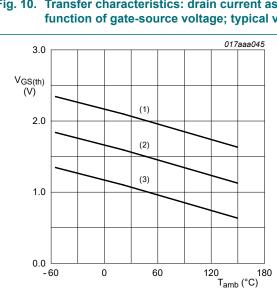


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of ambient temperature

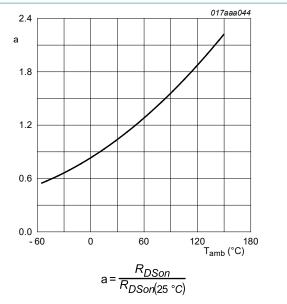
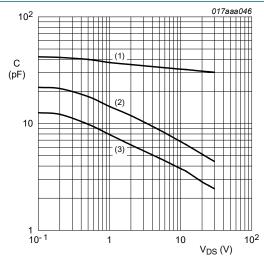


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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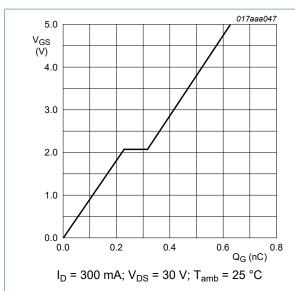


Fig. 14. Gate-source voltage as a function of gate charge; typical values

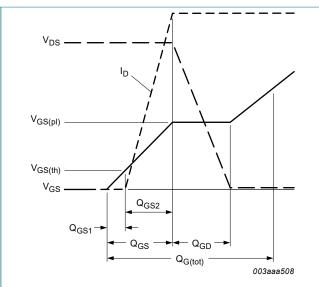
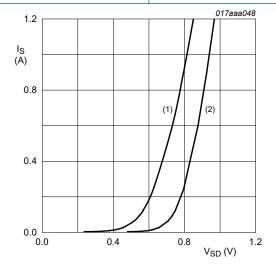


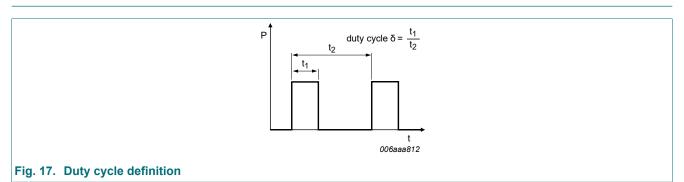
Fig. 15. Gate charge waveform definitions



V_{GS} = 0 V (1) T_{amb} = 150 °C (2) T_{amb} = 25 °C

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information



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Product data sheet

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12. Package outline

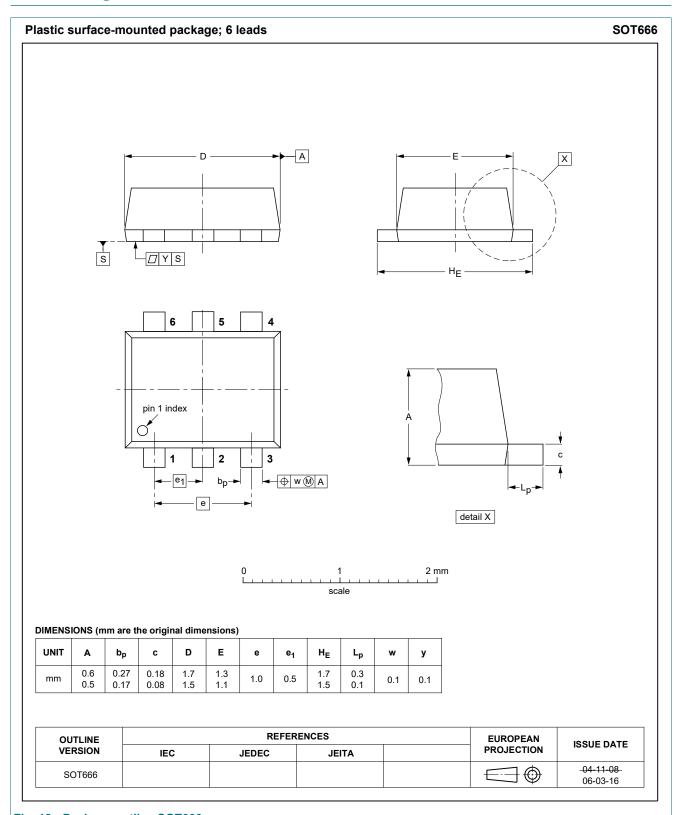
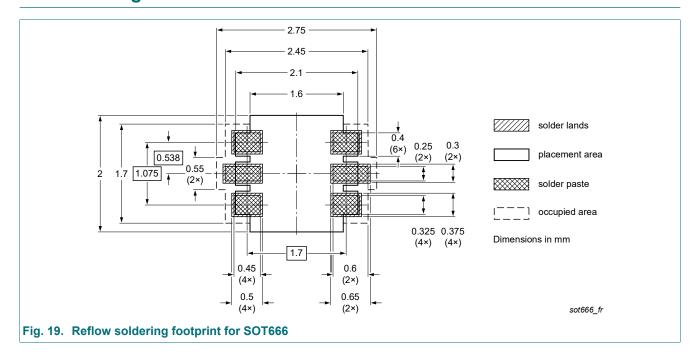


Fig. 18. Package outline SOT666

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13. Soldering



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14. Revision history

Table 8. Revision history

,							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
2N7002BKV v.4	20241017	Product data sheet	-	2N7002BKV v.3			
Modifications:	Chapter "Characteris	Chapter "Characteristics": Conditions corrected for Fig. 14					
2N7002BKV v.3	20221228	Product data sheet	-	2N7002BKV v.2			
2N7002BKV v.2	20100922	Product data sheet	-	2N7002BKV v.1			
2N7002BKV v.1	20100610	Product data sheet	-	-			

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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